

Silicon NPN Power Transistors

2SC3250

DESCRIPTION

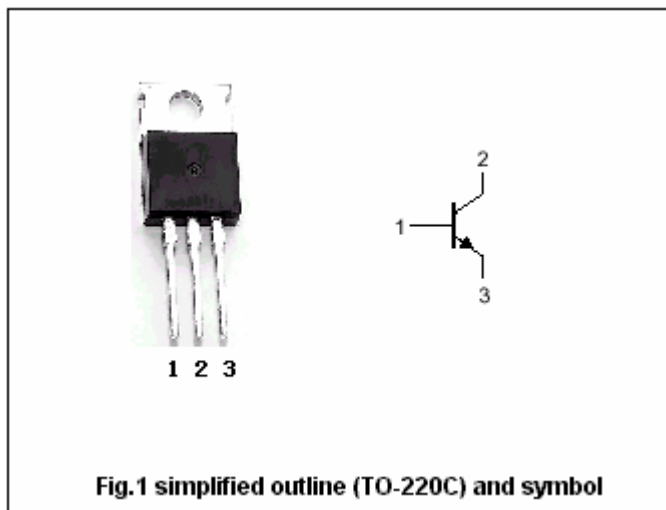
- With TO-220 package
- High V_{CEO}
- Large P_C

APPLICATIONS

- For TV video output amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.1	A
I_{CP}	Collector current-peak		0.2	A
P_C	Collector power dissipation	$T_c=25^\circ\text{C}$	15	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =0.1mA ; I _B =0	300			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =0.1mA ; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =0.1mA ; I _C =0	7			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =50mA ; I _B =5mA			1.5	V
V _{BE}	Base-emitter on voltage	I _C =30mA ; V _{CE} =10V			1.2	V
h _{FE-1}	DC current gain	I _C =5mA ; V _{CE} =50V	50		250	
h _{FE-2}	DC current gain	I _C =30mA ; V _{CE} =10V	30			
C _{OB}	Collector output capacitance	I _E =0 ; V _{CB} =30V, f=1MHz			5.0	pF
f _T	Transition frequency	I _E =-20mA ; V _{CB} =30V	70	100		MHz

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PACKAGE OUTLINE

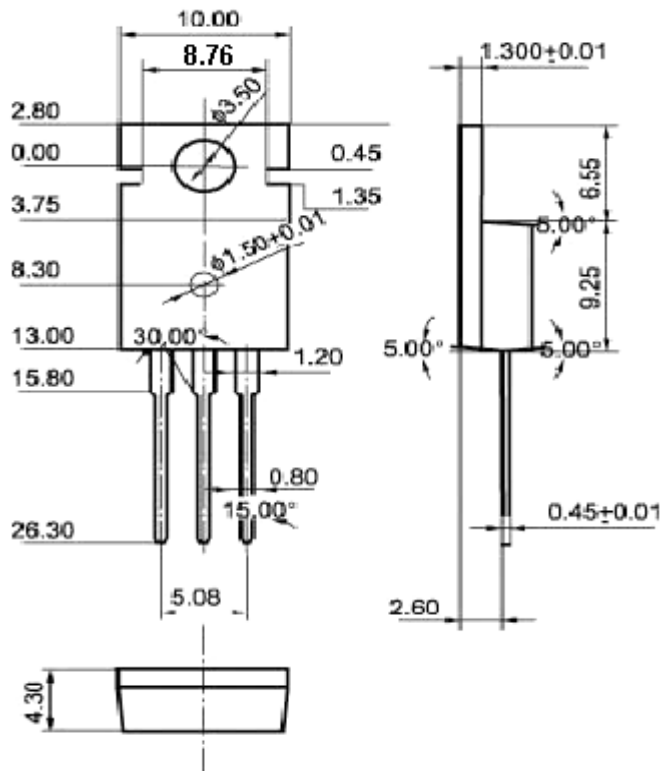


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)